

Список публикаций ведущей организации:

1. Emission Properties of Heavily Doped Epitaxial Indium-Nitride Layers / B.A. Andreev, D.N. Lobanov, L.V. Krasil'nikova, P.A. Bushuykin, A.N. Yablonskiy, A.V. Novikov, V. Yu. Davydov, P. A. Yunin, M. I. Kalinnikov, E.V. Skorohodov, Z.F. Krasil'nik, *Semicond.* 53, (2019) 1357–1362;
2. Towards the indium nitride laser: obtaining infrared stimulated emission from planar monocrystalline InN structures / B.A. Andreev, K.E. Kudryavtsev, A. N Yablonskiy, D.N. Lobanov, P.A. Bushuykin, L.V. Krasilnikova, E.V. Skorokhodov, P.A. Yunin, A.V. Novikov, V. Yu Davydov, Z.F. Krasilnik, *Scientific Reports* (2018) 9454;
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6. Особенности роста InN методом МПЭ с плазменной активацией азота при различных соотношениях потоков элементов III и V групп / Д.Н. Лобанов, А.В. Новиков, Б.А. Андреев, П.А. Бушуйкин, П.А. Юнин, Е. В. Скороходов, Л. В. Красильникова, *ФТП* **50** (2), (2016) 264–268.